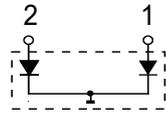


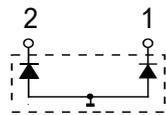
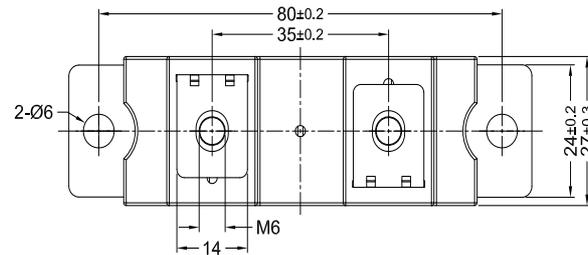
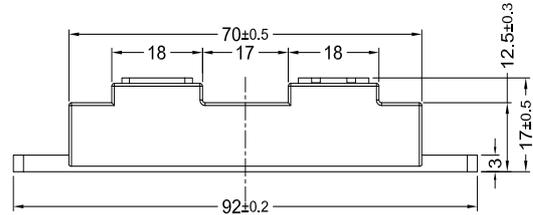
SRUD30040CTD3

Soft Recovery Behaviour Ultra Fast Recovery Epitaxial Diode Modules



Common Cathode
SRUD30040CTD3

Dimensions in mm



Common Anode
SRUD30040ATD3

	V _{RSM}	V _{RRM}
	V	V
SRUD30040CTD3	400	400
SRUD30040ATD3	400	400

Symbol	Test Conditions	Maximum Ratings	Unit
I _{FAVM} I _{FRMS}	T _C =125°C; rectangular,d=0.5,per module T _C =125°C; rectangular,d=0.5,per chip t _p <10us;rep.rating,pulse width limited by T _{VJM}	235 150 TBD	A
I _{FSM}	T _{VJ} =45°C per chip t=10ms(50HZ),sine t=8.3ms(60HZ),sine	2750 3100	A
	T _{VJ} =150°C per chip t=10ms(50HZ),sine t=8.3ms(60HZ),sine	2470 2790	
I ² t	T _{VJ} =45°C per chip t=10ms(50HZ),sine t=8.3ms(60HZ),sine	36500 37000	A ² S
	T _{VJ} =150°C per chip t=10ms(50HZ),sine t=8.3ms(60HZ),sine	29500 29970	
T _{VJ} T _{stg} T _{Hmax}		-40...+150 -40...+125 110	°C
P _{tot}		1300	W
M _d	Mounting torque(M6) Terminal connection torque(M6)	3.0-4.7/26-41 3.0-4.7/26-41	Nm/lb.in.
d _S d _A a	Creeping distance on surface Strike distance through air Maximum allowable acceleration	12.7 9.6 50	mm mm m/s ²
Weight		93	g



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Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I_R	$T_{VJ}=25^{\circ}\text{C}; V_R=V_{RRM}$ $T_{VJ}=25^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$ (per chip) $T_{VJ}=125^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		0.5 0.5 2	mA
V_F	$I_F=150\text{A}; T_{VJ}=125^{\circ}\text{C}$ $T_{VJ}=25^{\circ}\text{C}$ (per chip) $I_F=300\text{A}; T_{VJ}=125^{\circ}\text{C}$ $T_{VJ}=25^{\circ}\text{C}$	1.05 1.15 1.35 1.45	1.25 1.30 1.55 1.70	V
V_{FO}	For power-loss calculations only (per chip)		1.01	V
r_F	$T_{VJ}=125^{\circ}\text{C}$ (per chip)		2.85	m Ω
R_{thJC} R_{thJC}	Per Diode Per Module		0.150 0.100	K/W
t_{rr}	$I_F=1.0\text{A}; T_{VJ}=25^{\circ}\text{C}$ $I_F=150\text{A}; T_{VJ}=25^{\circ}\text{C}$	35 85	40 110	ns
I_{RM}	$I_F=200\text{A}; V_R=300\text{V}; -di/dt=200\text{A}/\mu\text{s}; T_{VJ}=25^{\circ}\text{C}$ $T_{VJ}=125^{\circ}\text{C}$ (per chip)	10 18		A A

FEATURES

- * International standard package
- * Copperbase plate
- * Planar passivated chips
- * Short recovery time
- * Low switching losses
- * RoHS compliant

APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Free wheeling diode in converters and motor control circuits
- * Inductive heating and melting
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * High reliability circuit operation
- * Low voltage peaks for reduced protection circuits
- * Low noise switching
- * Low losses



Sirectifier®

SRUD30040CTD3

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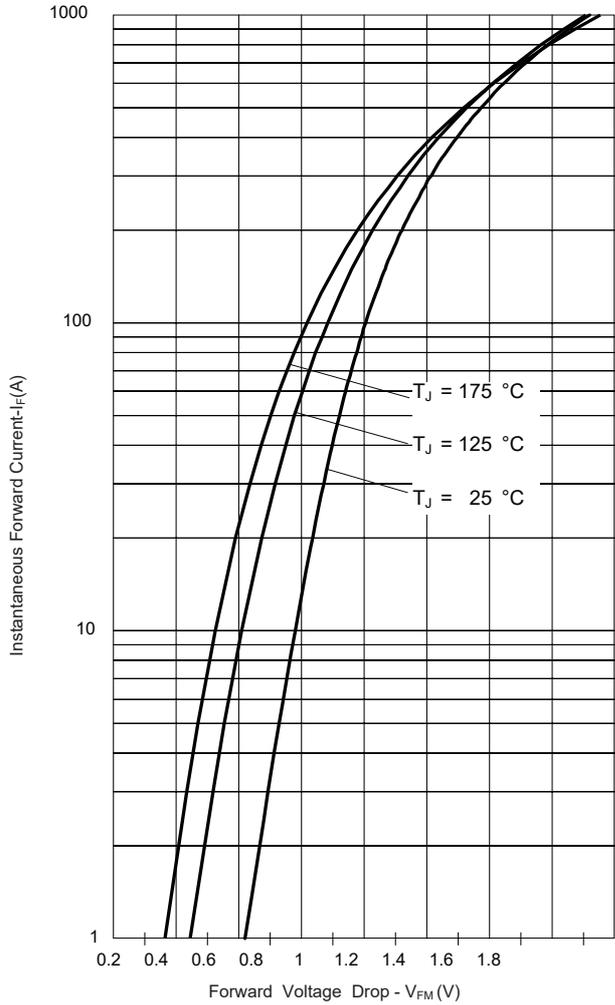


Fig. 1 Typical Forward Voltage Drop Characteristics

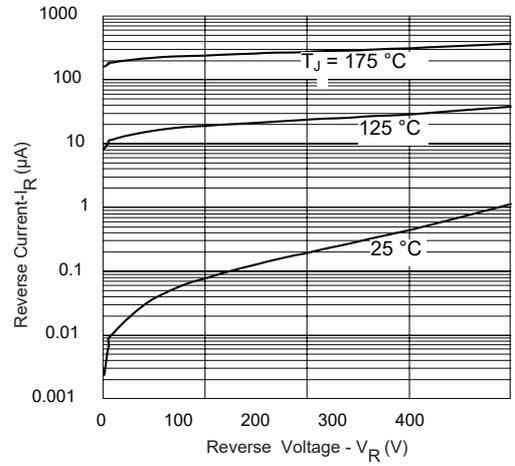


Fig. 2 Typical Values Of Reverse Current Vs. Reverse Voltage

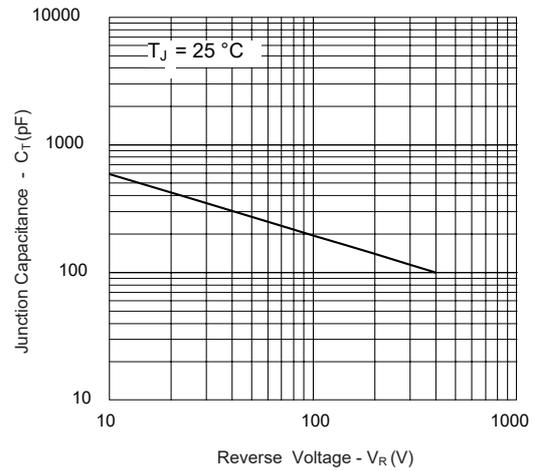


Fig. 3 Typical Junction Capacitance Vs. Reverse Voltage

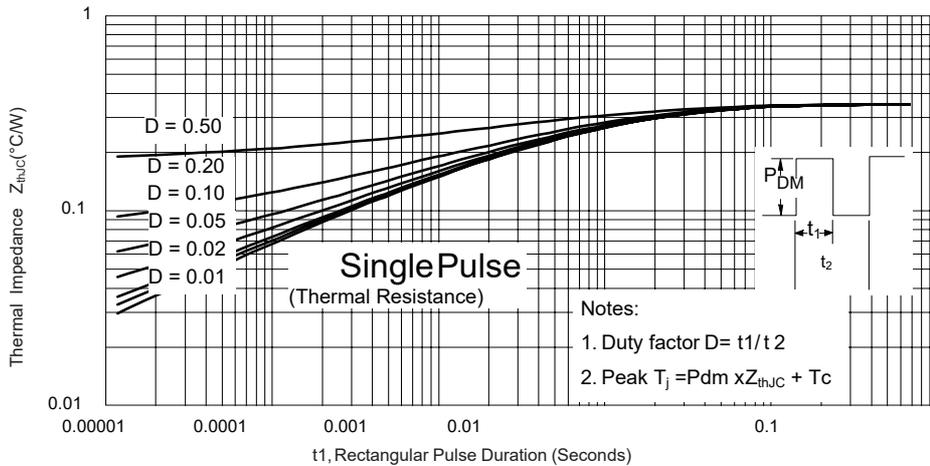


Fig. 4 Max. Thermal Impedance Z_{thJC} Characteristics

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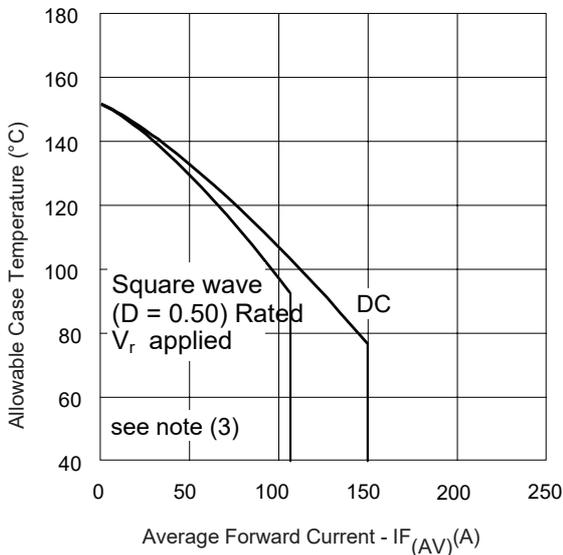


Fig.5 Max. Allowable Case Temperature Vs. Average Forward Current

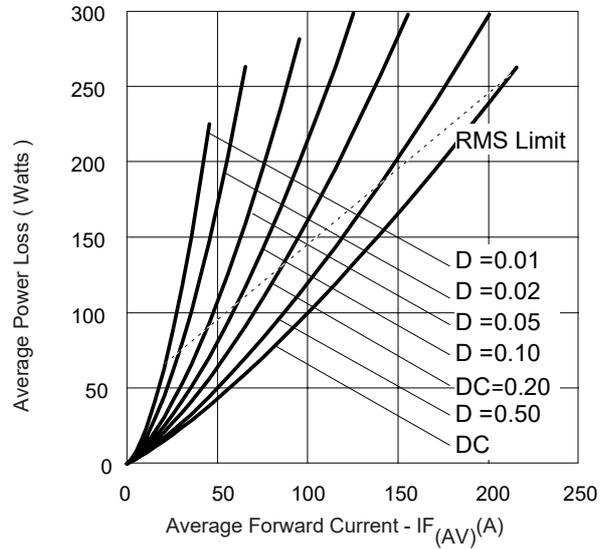


Fig.6 Forward Power Loss Characteristics

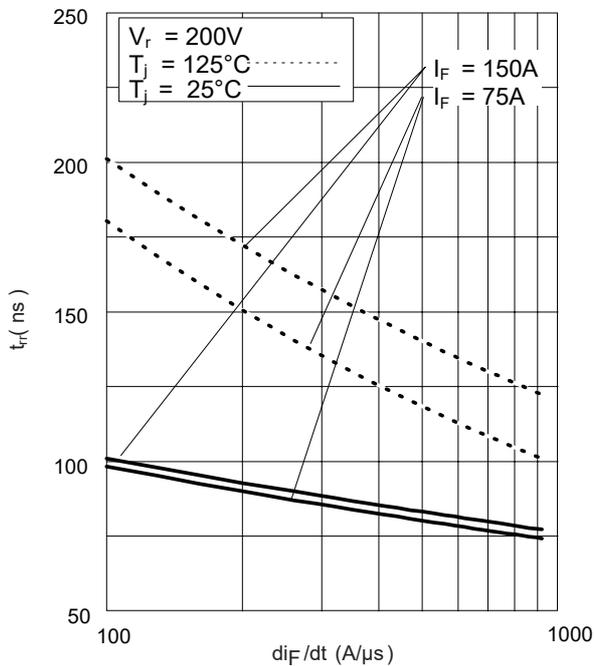


Fig.7 Typical Reverse Recovery time vs. di_F/dt

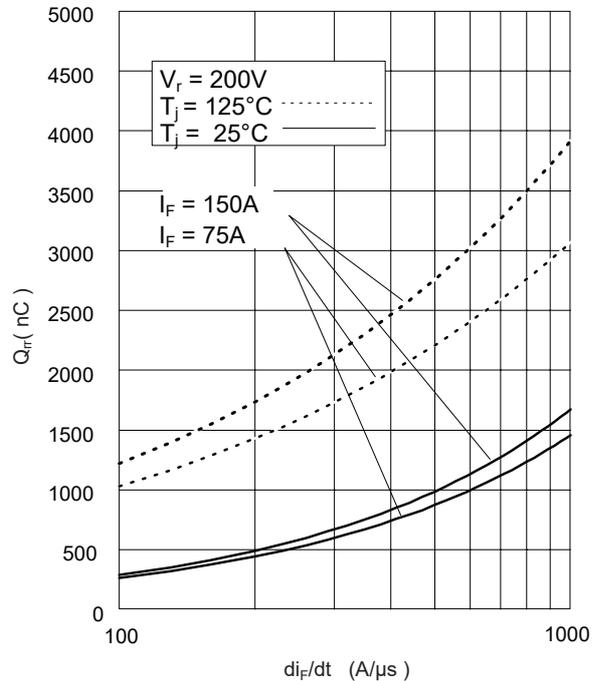


Fig.8 Typical Stored Charge vs. di_F/dt